

Potential and concentration-dependent self-assembly structure at solid/liquid interface

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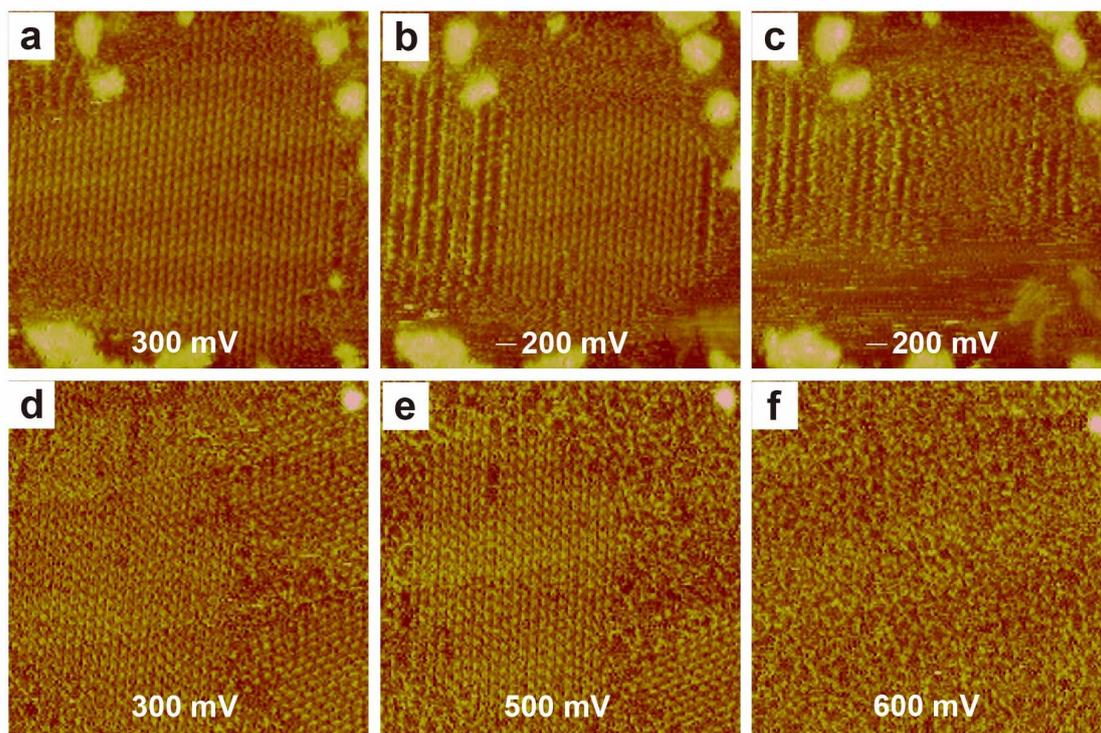


Figure S1. Series STM images of DDBDT rhombus structures on Au(111) surface at different potentials. Image conditions: (a) Scan area = $43 \times 43 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (b – c) Scan area = $43 \times 43 \text{ nm}^2$, $E_{\text{bias}} = -1030 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (d) Scan area = $42 \times 42 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (e – f) Scan area = $42 \times 42 \text{ nm}^2$, $E_{\text{bias}} = -529 \text{ mV}$, $I_t = 1.000 \text{ nA}$.

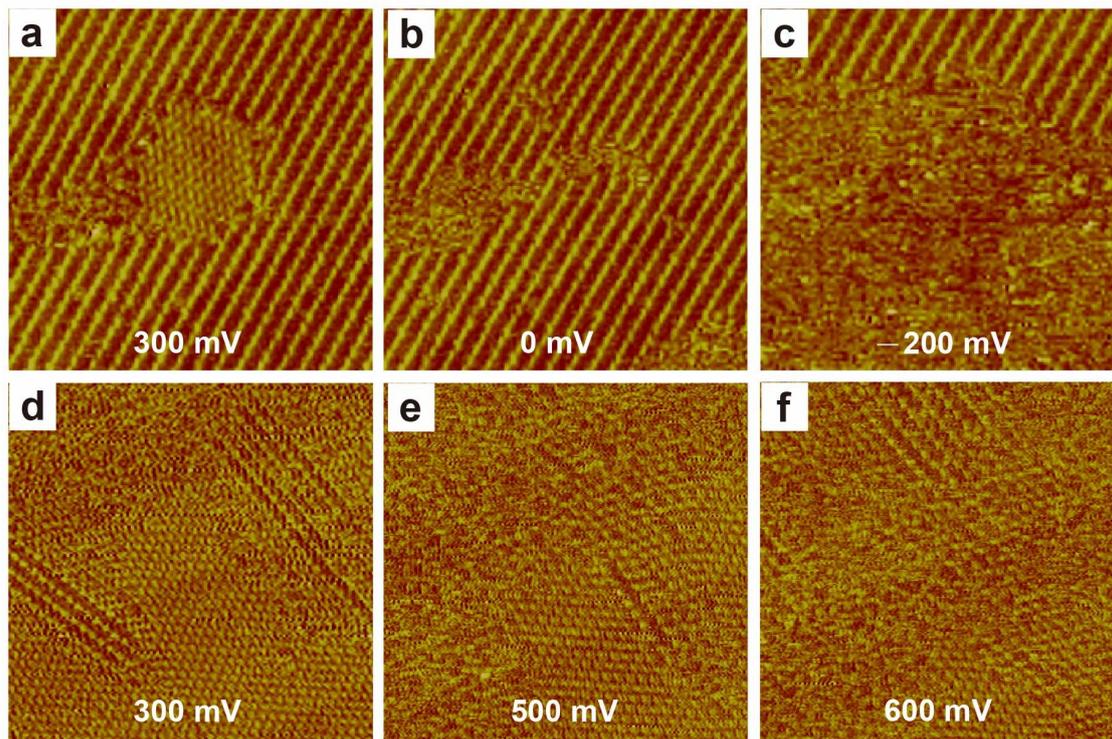


Figure S2. Series STM images of DDBDT two phase adlayer on Au(111) surface at different potentials. Image conditions: (a) Scan area = $32 \times 32 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (b – c) Scan area = $32 \times 32 \text{ nm}^2$, $E_{\text{bias}} = -771 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (d) Scan area = $42 \times 42 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (e – f) Scan area = $42 \times 42 \text{ nm}^2$, $E_{\text{bias}} = -404 \text{ mV}$, $I_t = 1.000 \text{ nA}$.

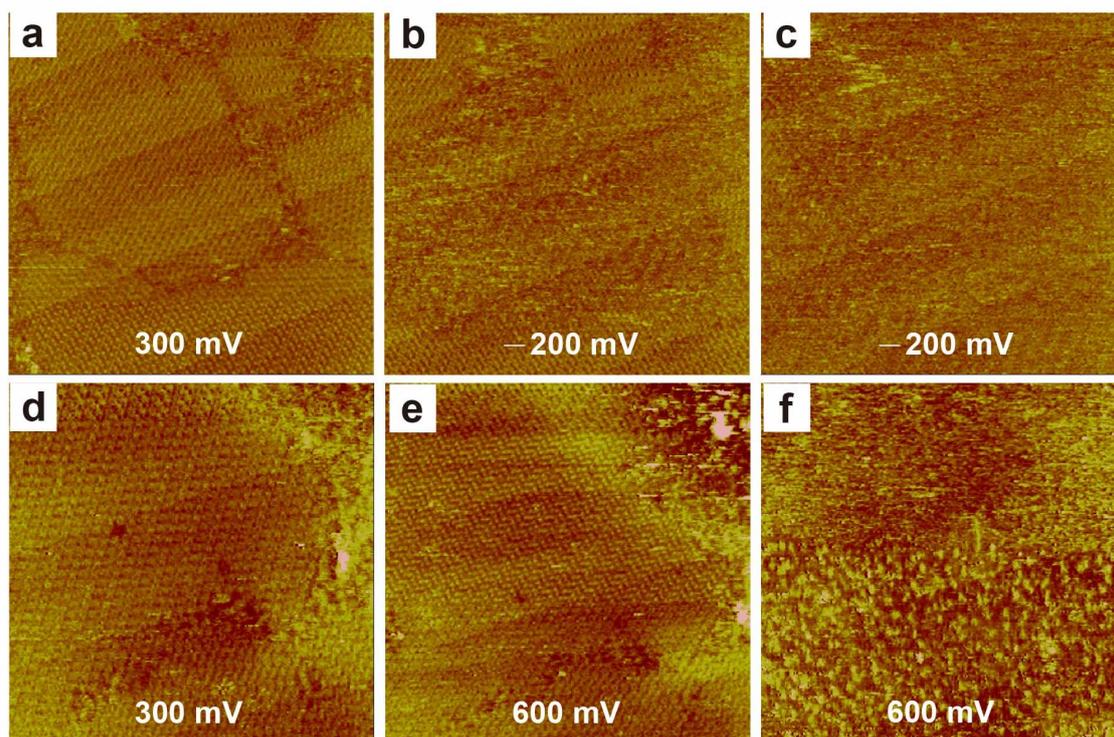


Figure S3. Series STM images of DDBDT herringbone structure on Au(111) surface at different potentials. Image conditions: (a) Scan area = $46 \times 46 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (b – c) Scan area = $46 \times 46 \text{ nm}^2$, $E_{\text{bias}} = -422 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (d) Scan area = $42 \times 42 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (e – f) Scan area = $42 \times 42 \text{ nm}^2$, $E_{\text{bias}} = -525 \text{ mV}$, $I_t = 1.000 \text{ nA}$.

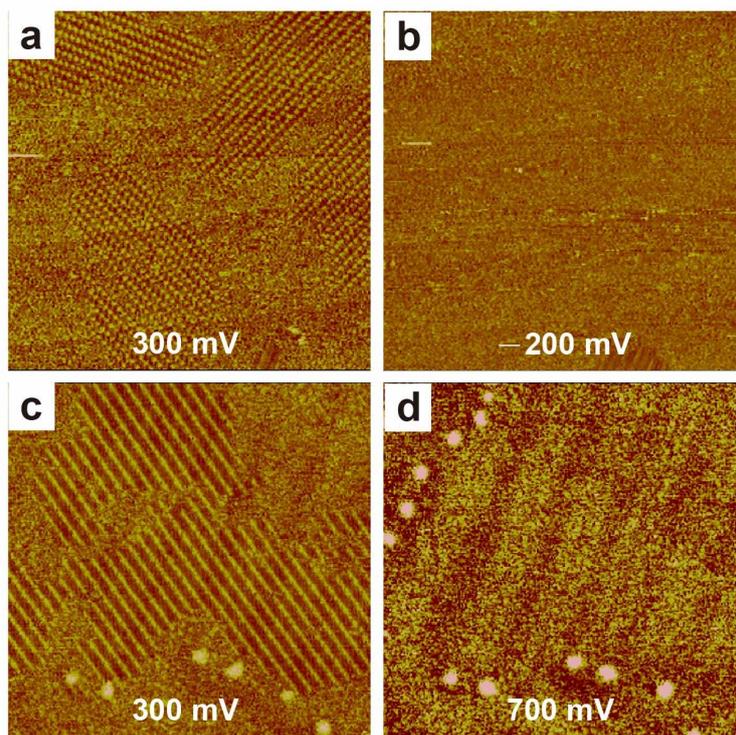


Figure S4. Series STM images of DDBDT lamellar structures on Au(111) surface at different potentials. Image conditions: (a) Scan area = $78 \times 78 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (b) Scan area = $78 \times 78 \text{ nm}^2$, $E_{\text{bias}} = -240 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (c) Scan area = $56 \times 56 \text{ nm}^2$, $E_{\text{bias}} = -200 \text{ mV}$, $I_t = 1.000 \text{ nA}$; (d) Scan area = $56 \times 56 \text{ nm}^2$, $E_{\text{bias}} = -1050 \text{ mV}$, $I_t = 1.000 \text{ nA}$.

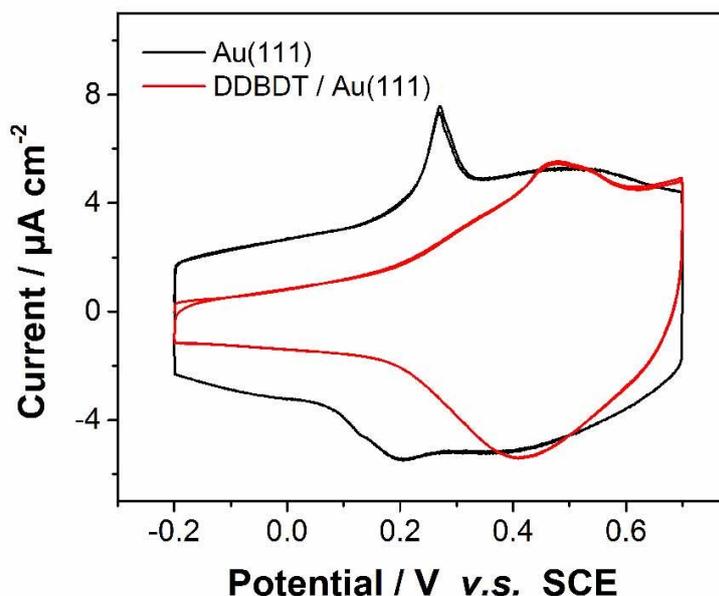


Figure S5. (a) Typical cyclic voltammograms of Au(111) electrode in 0.1 M HClO₄ before (black line) and after (red line) the addition of 10⁻⁵ M DDBDT. Scan rate is 50 mV/s.

Figure S5 displays typical cyclic voltammograms (CVs) of bare (black line), DDBDT adlayer (red line) modified Au(111) electrodes in 0.1 M HClO₄ recorded at the scan rate of 50 mV/s. The voltammogram for bare Au(111) electrode in the double-layer potential region is identical to previous reports^{1, 2}. A pair of redox peak around 0.30 V can be observed, which is referred to the lift of the ($22 \times \sqrt{3}$) reconstruction of Au(111) surface. For the DDBDT modified Au(111) electrode, the double-layer charging current decrease obviously, which indicating the adsorption of DDBDT adlayer (red line). The DDBDT adlayer is stable in the featureless double-layer charging region between -0.2 and 0.2 V. Reversible oxidative and reductive peaks can be distinguished at *ca.* 440 mV, which indicate that redox reactions happened at this substrate potential.

References

1. H. Honbo, S. Sugawara and K. Itaya, *Anal. Chem.*, 1990, **62**, 2424.
2. H. Angerstein-Kozłowska, B. E. Conway, A. Hamelin and L. Stoicoviciu, *J. Electroanal. Chem. Interfacial Electrochem.*, 1987, **228**, 429.